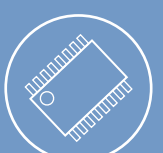


RF & Wireless Semiconductors



2010

CEL California Eastern Laboratories

California Eastern Laboratories serves designers, OEMs and contract manufacturers in the RF & Wireless, Mobilecomm, Multimedia, Broadband Communications, Industrial Control, and Automated Test Equipment (ATE) markets. With over 50 years experience in high frequency design, customer support and fulfillment, CEL is ideally positioned to provide its customers with solutions tailored to meet their specific needs.

CEL product lines include:

RF & Wireless Semiconductors**802.15.4 / ZigBee Transceiver ICs & Modules****Optocouplers & Solid State Relays****Fiber Optic Lasers & Detectors**

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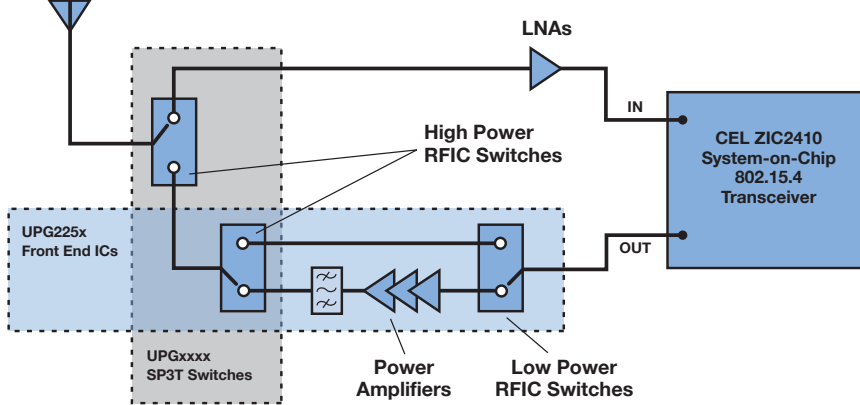
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Front End Components for 450 MHz to 2.5 GHz Applications

Wi-Fi • Bluetooth • ZigBee • Automated Meter Reading • Mesh & Home Area Networks • ISM Band applications



Front End ICs		450 MHz	915 MHz	2.4 GHz
UPG2253T6S	+19 dBm GaAs RFIC: PA, 2 SPDTs, filter, Tx/Rx bypass path			✓
UPG2254T6W ¹	+20 dBm GaAs RFIC: Low cost version of UPG2253, miniature pkg			✓
MMIC & Transistor Power Amplifiers				
UPG2118K	+31.5 dBm Three Stage GaAs MMIC	✓	✓	✓
UPG2250T5N	+25 dBm GaAs MMIC, operates at 1.8 or 3.0 V		✓	✓
UPG2301T5L	+23 dBm Two stage GaAs HBT		✓	✓
UPG2314T5N	+20 dBm Low current GaAs MMIC		✓	✓
UPG2251T6M	+25 dBm GaAs MMIC, fully matched			✓
NE5500234	Silicon LD-MOSFET: 32.5 dBm Pout typ	✓	✓	
NE5511279A	Silicon LD-MOSFET: 40 dBm Pout typ	✓	✓	
NE5531079A	Silicon LD-MOSFET: 40 dBm Pout typ	✓	✓	
NESG250134	0.8 Watt SiGe HBT	✓	✓	
NESG260234	1 Watt SiGe HBT	✓	✓	
NESG270034	2 Watt SiGe HBT	✓	✓	
NE5520379A	3 watt LDMOS FET: 35.5 dBm Pout typ	✓	✓	
NE664M04	0.4 Watt Silicon Bipolar Transistor Driver	✓	✓	✓
NE5520279A	LDMOS FET: 32 dBm Pout typ	✓	✓	✓
NESG2101M05	120 mW SiGe Bipolar Transistor Driver	✓	✓	✓
Medium & High Power GaAs RFIC Switches				
UPG2155TB	SPDT, low harmonics, ideal for high power applications	✓	✓	
UPG2009TB	SPDT, high power, high linearity, <i>no compromise</i> performance	✓	✓	✓
UPG2015TB	SPDT, medium power, single control	✓	✓	✓
UPG2030TK	SPDT, great all-around med power device, in mini flat-lead pkg	✓	✓	✓
UPG2179TB	SPDT, industry s best low cost, med power switch, industry standard pkg	✓	✓	✓
UPG2406TK/T6R	SPDT, medium power, choice of packages	✓	✓	✓
UPG2404T6Q	SP3T, high power, ideal for triple mode cellular phone, NFC	✓	✓	
UPG2405T6Q	SP3T, miniature package for Bluetooth, WLAN, NFC	✓	✓	✓
UPG2413T6M/T6Z	SP3T, medium power, low insertion loss, low profile package	✓	✓	✓
UPG2150T5L	SP3T, 35dB isolation between WLAN & B tooth ports		✓	✓
Low Power CMOS & GaAs RFIC Switches				
UPD5713TK	Low cost CMOS SPDT, single control, low profile package	✓	✓	
UPG2159T6R	SPDT, low insertion loss, high isolation, 1.8 or 3 V		✓	✓
UPG2012TB/TK	Single control GaAs SPDT, TB or mini flat-lead TK package	✓	✓	✓
UPG2214TB/TK	Low cost GaAs SPDT, performance guaranteed at 1.8 & 3.0 Volts	✓	✓	✓

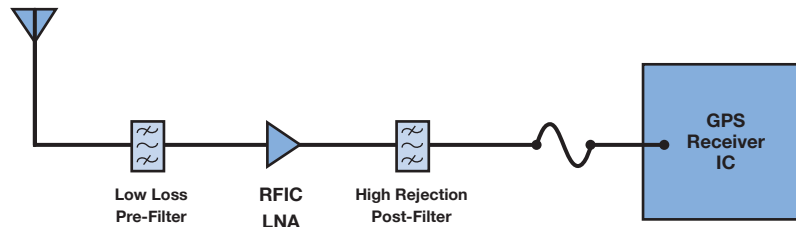
Notes: 1. Under development, please inquire

Front End Components for 450 MHz to 2.5 GHz *continued*

MMIC & Transistor LNAs (Performance @ 1GHz)		450 MHz	915 MHz	2.4 GHz
UPD5740T6N	Wideband CMOS LNA IC with bypass for mobile DTV	✓	✓	
UPC3237TK	SiGe:C RFIC: 1.4dB NF, 15.3dB Gain, for DTV	✓	✓	
NE662M04	Silicon Bipolar Transistor: 1.0dB NF, 21 dB Gain	✓	✓	✓
NESG2031M05	SiGe Bipolar Transistor: 0.7dB NF, 23dB Gain		✓	✓
NESG3031M05	SiGe Bipolar Transistor: 0.6dB NF, 16dB Gain		✓	✓
UPC8233TK	SiGe:C RFIC: 0.95dB NF, 20dB Gain, 1.8V VCC		✓	✓
UPG2310TK	Two stage GaAs MMIC: 1.7 dB NF, 25.5dB Gain, 28.5dBm OIP ₃		✓	✓
NESG3032M14	SiGe Bipolar Transistor: 0.6dB NF, 17.5dB Gain		✓	✓
NESG3033M14	SiGe Bipolar Transistor: 0.6dB NF, 17.5dB Gain, ESD protection		✓	✓
NE3508M04	GaAs FET: 0.4dB NF, 14dB Gain			✓

RFIC LNAs for Improved GPS Signal Performance

External LNAs reduce front-end noise and improve receiver sensitivity. Combined with tuning and distributed filtering they can improve noise performance by more than 1.5dB over on-chip LNAs.



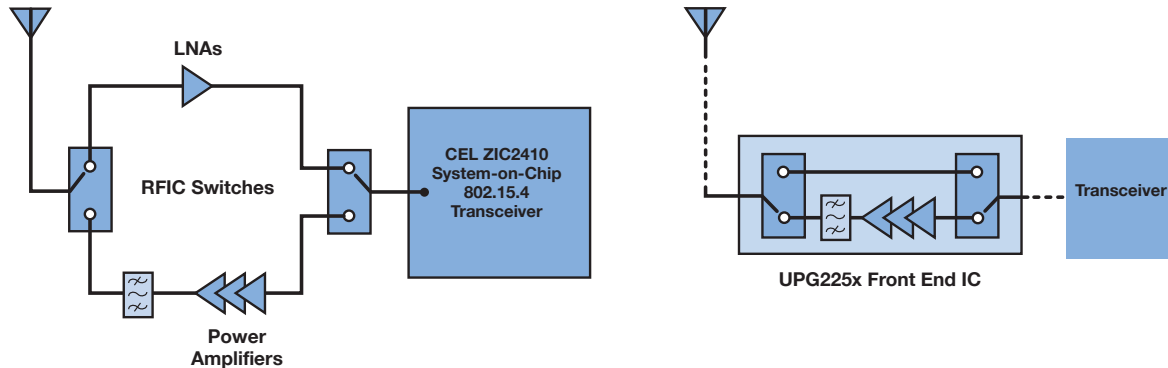
SiGe & SiGe:C RFIC LNAs

Part Number	Description	Supply Voltage (V)	ICC (mA)	Noise Figure (dB)	Gain (dB)	IIP ₃ (dBm)	Total External Components Req d	Package
UPC8211TK	Low current	3.0	3.5	1.30	18.5	-12	9	TK
UPC8215TU	High gain, highly integrated	3.0	10	1.30	27	-14.5	4	TU
UPC8230TU	Low noise & distortion, highly integrated	3.0	6.0	0.85	18.5	-5	5	TU
UPC8231TK	Low noise & current, high gain	3.0	3.8	0.80	20	-10	9	TK
UPC8232T5N	Low noise & current, highly integrated	3.0	3.0	0.95	17	-8	5	T5N low profile
UPC8233TK	Low voltage, current & noise, high gain	2.7	3.5	0.90	20	-8.5	8	TK
UPC8236T6N	Low voltage, noise & distortion, highly integrated	2.7	6.5	0.80	19.5	-3	5	T6N low profile
UPC8240T6N	Low voltage & noise, high gain, highly integrated	2.7	6.5	1.0	28	-21.5	5	T6N low profile
UPC8244T6N ¹	Low voltage, noise & distortion, adjustable current, gain & IIP ₃	2.7	3 - 10	0.90	14.5-18.5	0 - +5	7	T6N low profile

Notes: 1. Under development, please inquire

Range Extension Components for 802.15.4/ZigBee Applications

Our Power Amplifiers, LNAs and RFIC Switches are designed to integrate easily with a wide variety of 802.15.4, ZigBee and Bluetooth transceivers ICs including our own ZIC2410 *MeshConnect* System-on-Chip transceivers.



Front End ICs

UPG2253T6S	+19dBm GaAs RFIC: PA, 2 SPDTs, filter, Tx/Rx bypass path
UPG2254T6W ¹	+20dBm GaAs RFIC: Low cost version of UPG2253, miniature pkg

GaAs MMIC Power Amplifiers

UPG2118K	+31.5dBm P _{OUT} , 50% PAE
UPG2250T5N	+20 dBm P _{OUT} @ 1.8 V _{DD} , 50% PAE
UPG2251T6M	+25dBm P _{OUT} @ 3.0V, 47% PAE, with matching circuit
UPG2314T5N	+20dBm P _{OUT} , 65mA operating current, 50% PAE, 20dB variable gain control
UPG2301T5L	+23dBm P _{OUT} , 50% PAE, 20dB variable gain control

GaAs RFIC SPDT Switches

UPG2012TK	Low power, single control voltage
UPG2015TB	Medium power, single control voltage, industry-standard package
UPG2030TK	Low insertion loss, high isolation
UPG2158T5K	Medium power, 1.8/2.7V control voltage, miniature ultra-thin package
UPG2179TB	Industry's best medium power SPDT
UPG2214TB/TK	1.8/3.0V control voltage, low insertion loss, high isolation
UPG2406T6R	Medium power, 1.8 V control voltage, 0.45dB Insertion Loss, +22.0dBm P _{IN(0.1dB)}
UPG2406TK	Medium power, 1.8/2.7V control voltage, 0.45dB Insertion Loss
UPG2408TK	Medium power, 0.48dB Insertion Loss, 29dBm P _{IN(0.1dB)}

Transistor & MMIC LNAs

NE662M04	Silicon NPN transistor, 1.3dB noise figure, 15dB gain
NE3508M04	GaAs HJ FET, super low 0.45dB noise figure, 14dB gain
UPC8233TK	SiGe:C MMIC, 1.8 to 3.3V control voltage, 1.1 dB noise figure, 16.5dB gain
NESG2031M05	SiGe HBT, 0.9dB noise figure, 17dB gain
NESG3031M05/M14	SiGe HBT, 0.6dB noise figure, 16dB gain

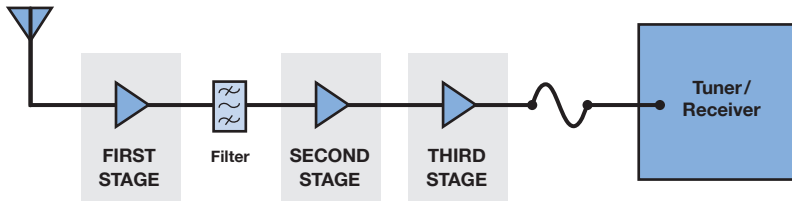
CEL System-on-Chip Transceiver IC

ZIC2410	RF Transceiver with 8051 MCU: +8dBm output power, 106dB link budget, scalable data rates to 1Mbps, voice CODEC, 48 pin QFN or 72 pin VFBGA package
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Notes: 1. Under development, please inquire

Low Noise Amplifiers for L to C-Band Applications

First, second and third stage devices for applications from 1 to 8GHz



LNAs by Application

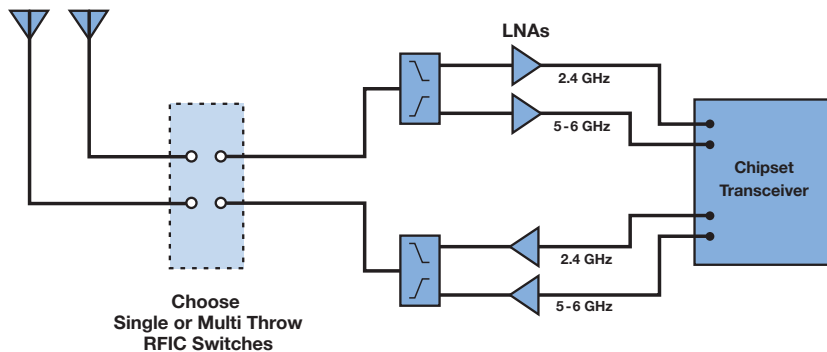
Application	Frequency	FIRST STAGE	SECOND STAGE	THIRD STAGE
GPS	1.575 GHz	* UPC8211TK UPC8215TU UPC8230TU UPC8231TK UPC8232T5N UPC8233TK UPC8236T6N UPC8240T6N UPC8244T6N		
		NE3508M04 NE3509M04/M14 NESG2031M05	NE662M04 NESG2031M05	
DAB and Satellite Radio	1.4 2.35GHz	NE3508M04 NE3509M04 NE3510M04	NE3508M04 NESG2101M05 NESG2031M05 NESG3031M05 NESG3032M14 NE662M04	NE3508M04 NESG2101M05
WLAN, Wi-Fi, Cordless Phone	2.4GHz	NESG2031M05 NESG3031M05 NESG3032M14 NESG3033M14	NESG2031M05 NESG3031M05 NESG3032M14 NESG3033M14	
WLAN, Wi-Fi, Cordless Phone	5 6GHz	NESG2031M05 NESG2101M05 NESG3031M05 NESG4030M14	NESG2031M05 NESG2101M05 NESG3031M05 NESG4030M14	

LNA Performance (see Data Tables for additional specifications)

Part Number	Description	NF (dB)	Gain (dB)	P1dB (dBm)	Package
* Low Noise, High Gain Silicon RFIC LNAs (specified @ 1.575GHz)					
UPC8211TK	SiGe RFIC	1.3	18.5	-24	TK
UPC8215TU	SiGe RFIC	1.3	27.0	-22	TU
UPC8230TU	SiGe:C RFIC	0.85	18.5	-17	TK
UPC8231TK	SiGe:C RFIC	0.8	20.0	-22	TK
UPC8232T5N	SiGe:C RFIC	0.95	17.0	-22	T5N
UPC8233TK	SiGe:C RFIC	0.95	20.0	-23	TK
UPC8236T6N	SiGe:C RFIC	0.8	19.5	-18	T6N
UPC8240T6N	SiGe:C RFIC	1.0	28.0	-22.5	T6N
UPC8244T6N ¹	SiGe:C RFIC	1.0	19.0		T6N
NE3508M04	GaAs HJ-FET	0.40 @ 2.0GHz	14.0 @ 2.0GHz	+18.0	M04
NE3509M04/M14 ²	GaAs HJ-FET	0.40 @ 2.0GHz	17.5 @ 2.0GHz	+14.0	M04 or M14
NE3510M04	GaAs HJ-FET	0.35 @ 2.0GHz	19.0 @ 2.0GHz	+12.0	M04 or M14
NE662M04	Silicon Transistor	1.1 @ 2.0GHz	16.0 @ 2.0GHz		M04
NESG2021M05/M16	SiGe Transistor	0.9 @ 2.0GHz	18 @ 2.0GHz	+9	M05 or M16
NESG2031M05	SiGe Transistor	0.8 @ 2.0GHz	17 @ 2.0GHz	+13	M05
NESG2101M05	SiGe Transistor	0.9 @ 2.0GHz	13 @ 2.0GHz	+21	M05
NESG3031M05/M14	SiGe Transistor	0.6 @ 2.4GHz	16 @ 2.4GHz	+13	M05 or M14
NESG3032M14	SiGe Transistor	0.6 @ 2.0GHz	17.5 @ 2.0GHz	+12.5	M14
NESG3033M14	SiGe Transistor	0.6 @ 2.0GHz	17.5 @ 2.0GHz	+12.5	M14
NESG4030M14	SiGe Transistor	1.1 @ 5.8GHz	11.5 @ 5.8GHz	+9	M14

Notes: 1. Adjustable current device, under development, please inquire 2. NE3509M14 under development, please inquire

Single and multi-throw switches and discrete Silicon and GaAs low noise amplifiers designed specifically for Dual Band WLAN



GaAs RFIC Switches to 2.5GHz Single & Multi Throw

UPG2179TB	SPDT, 0.3dB Insertion Loss @ 2GHz, industry-standard package
UPG2158TK	SPDT, 1.8 or 2.7V control voltage, 0.45dB Insertion Loss @ 2GHz
UPG2406T6R	SPDT, 0.45dB Insertion Loss @ 2GHz, +22.0dBm PIN(0.1dB) @ +1.8VCONT
UPG2406TK	SPDT, 1.8 or 2.7V control voltage, 0.45dB Insertion Loss @ 2GHz
UPG2418TB¹	SPDT, 50Ω termination, 0.45dB Insertion Loss, 21dB Isolation @ 2.5GHz
UPG2150T5L	SP3T, 0.5dB Insertion Loss, 35dB Isolation between ports @ 2.5GHz
UPG2405T6Q	SP3T, 0.60dB Insertion Loss, 20dB Isolation @ 2.5GHz
UPG2413T6M	SP3T, 0.5dB Insertion Loss, 18dB Isolation @ 2.5GHz, 12 pin package
UPG2413T6Z	SP3T, 0.5dB Insertion Loss, 18dB Isolation @ 2.5GHz, 8 pin package

GaAs RFIC Switches Broadband to 6GHz

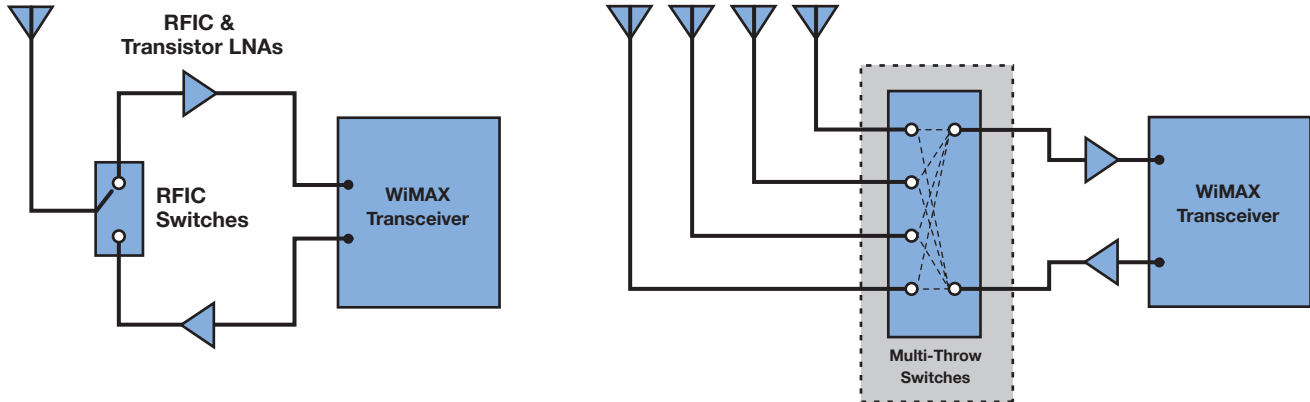
UPG2163T5N	SPDT, Insertion Loss: 0.4 dB @ 2.4GHz, 0.5 dB @ 6GHz
UPG2185T6R	SPDT, Insertion Loss: 0.4 dB @ 2.5GHz, 0.5 dB @ 6GHz, 25dB Isolation @ 6GHz
UPG2411T7C¹	SPDT for Dual Band WLAN, Insertion Loss: 0.6 dB @ 2.5GHz, 0.8 dB @ 6GHz
UPG2411T6X¹	SPDT for Dual Band WLAN, Insertion Loss: 0.4 dB @ 2.5GHz, 0.5 dB @ 6GHz
UPG2415TK / T6X	SPDT for Dual Band WLAN, high power, low insertion loss for Access Point applications
UPG2162T5N	DPDT, Insertion Loss: 0.6dB @ 2.4GHz, 0.85dB @ 5.5GHz
UPG2164T5N	DPDT, Insertion Loss: 0.5dB @ 2.4GHz, 0.7dB @ 5.5GHz

LNAs

NESG2031M05	Low cost SiGe HBT, 0.9dB Noise Figure, 16dB Gain @ 2.4GHz
NESG3031M05 / M14	SiGe HBT, 1.1 dB Noise Figure, 9.5dB Gain @ 2.4GHz
NESG3032M14	SiGe HBT, 0.6dB Noise Figure, 17.5dB Gain @ 2.0GHz
NESG3033M14	SiGe HBT, 0.6dB Noise Figure, 17.5dB Gain @ 2.0GHz, built-in ESD protection
NESG4030M14	SiGe HBT, 1.1 dB Noise Figure, 11.5dB Gain @ 5.8GHz, built-in ESD protection

Notes: 1. Under development, please inquire

Single and multi-throw switches and transistor and RFIC low noise amplifiers designed specifically for WiMAX



GaAs RFIC Switches

UPG2176T5N	SPDT 2.4 6GHz, Insertion Loss: 0.5dB @ 2.4GHz, 0.7dB @ 5.5GHz, internal termination
UPG2157T5F	SPDT 2.4 6GHz, Insertion Loss: 0.6dB @ 2.4GHz, 0.85dB @ 5.5GHz, internal termination
UPG2409TB	SPDT 2.0 4.0GHz, Insertion Loss: 0.45dB @ 2.5GHz, 0.6dB @ 3.8GHz
UPG2409T6X	SPDT 2.0 6.0GHz, Insertion Loss: 0.45dB @ 2.5GHz, 0.65dB @ 6.0GHz
UPG2181T5R	+40dBm DP4T for antenna diversity and Tx/Rx switching, 1dB Insertion Loss, 24dB Isolation @ 3.5GHz

Transistor & RFIC LNAs

NESG3031M05 / M14	High fr SiGe HBT, 0.6dB Noise Figure, 16dB Gain @ 2.5GHz
NE3508M04	GaAs HJ FET, super low 0.45dB noise figure, 14dB gain @ 2.5GHz
UPG2310TK	Two stage GaAs MMIC: 1.7dB NF, 25.5dB Gain, 23.5dBm OIP ₃ @ 2.5GHz

SPDT Dual Control Switches

Part Number	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25 C) Frequency range: 0.1 to 2.5 GHz						Package Code
	Features	Control Voltages (V)	Insertion Loss @2GHz (dB)	Isolation @2GHz (dB)	Input Power @0.1 dB compression point	Input Power @1.0 dB compression point	
UPG2009TB	High Power/High Linearity	+2.8/0	0.30	28	34 dBm	NA	TB
UPG2030TK	Medium Power, Versatile	+2.8/0	0.30	27	27 dBm	30 dBm	TK
UPG2155TB	High Power, Low Harmonics	+2.6/0	0.40	19	37 dBm	NA	TB
UPG2158T5K	Medium Power, Small Pkg	+1.8, 2.7/0	0.45	19	29 dBm	30.5 dBm	T5K
UPG2159T6R	Low Insertion Loss, Small Pkg	+1.8, 2.7/0	0.23	27	22 dBm	25.5 dBm	T6R
UPG2179TB	Industry's best medium power	+3.0/0	0.30	27	29 dBm	32 dBm	TB
UPG2214TB	Hi Performance @ 3.0 or 1.8V	+1.8, 3.0/0	0.30	27	23 dBm	20 (1.8V), 26 (3.0V)	TB
UPG2214TK	Hi Performance @ 3.0 or 1.8V	+1.8, 3.0/0	0.30	27	23 dBm	20 (1.8V), 26 (3.0V)	TK
UPG2406TK	Medium Power, L, S Band	+1.8, 2.7/0	0.45	19	29 dBm	25 (1.8V), 30.5 (3.0V)	TK
UPG2406T6R	Medium Power, Small Pkg	2.7/0	0.45	19	29 dBm	30.5	T6R
UPG2408TK	Medium Power	+3.0/0	0.48	19	29 dBm	—	TK
UPG2418TB	Internally terminated	+3.0/0	0.45	21	29 dBm	32 dBm	TB

SPDT Single Control Switches

Part Number	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25 C) Frequency range: 0.1 to 2.5 GHz						Package Code
	Features	Control Voltages (V)	Insertion Loss @ 2GHz (dB)	Isolation @ 2GHz (dB)	Input Power @ 0.1 dB compression point	Input Power @ 1.0 dB compression point	
UPD5713TK	Low Cost CMOS	+2.8/0	0.80	25	17 dBm	21 dBm	TK
UPG2010TB	High Power	+2.8/0	0.30	28	33 dBm	NA	TB
UPG2012TB	Low Power	+2.8/0	0.30	28	20.5 dBm	24 dBm	TB
UPG2012TK	Miniature, Low Power	+2.8/0	0.30	28	20.5 dBm	24 dBm	TK
UPG2015TB	Medium Power	+2.8/0	0.30	28	27 dBm	30 dBm	TB
UPG2156TB	High Power	+2.6/0	0.45	17.5	37 dBm	NA	TB
UPG2160T5K	Miniature, Low Power	+2.6/0	0.35	18	21 dBm	NA	T5K

Single & Multi-Throw Switches

Part Number	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25 C)						Package Code
	Features	Control Voltages (V)	Insertion Loss (dB)	Isolation (dB)	Input Power @ 0.1 dB compression point	Input Power @ 1.0 dB compression point	
UPG2150T5L	SP3T/WLAN, B Tooth	+2.85/0	0.50@2.5 GHz	35@2.5 GHz	NA	+25dBm ¹ +31dBm ²	T5L
UPG2181T5R	DP4T / WiMAX	+3.0/0	1.0@3.8GHz	24@3.8GHz	NA	40Tx / 35Rx dBm	T5R
UPG2183T6C	SP4T / High Power	+3.0/0	0.4@0.9GHz 0.55 @ 2 GHz	24 @ 0.9GHz 19 @ 2 GHz	+37.5dBm @ 0.9GHz +35dBm @ 2 GHz	NA	T6C
UPG2189TB	SPST / High Power	+2.6 / 0	0.35 @ 2 GHz	13.5 @ 2 GHz	+37 dBm	NA	TB
UPG2404T6Q	SP3T / High Power	+2.8/0	0.55 @ 2 GHz	21 @ 2 GHz	+33dBm	NA	T6Q
UPG2405T6Q	SP3T / WiFi, B Tooth	+2.8/0	0.60 @ 2.5 GHz	20 @ 2.5 GHz	+31dBm	NA	T6Q
UPG2413T6M	SP3T / Med Power	+3.0/0	0.4 @ 1GHz 0.5 @ 2.5 GHz	26 @ 1 GHz 18 @ 2.5 GHz	+28dBm	+33 dBm	T6M
UPG2413T6Z	SP3T / Med Power	+3.0/0	0.4 @ 1GHz 0.5 @ 2.5 GHz	26 @ 1 GHz 18 @ 2.5 GHz	+28dBm	+31 dBm	T6M
UPG2416T7B ³	SP4T no blocking caps	+1.3 min	0.5 @ 2 GHz	20 @ 2 GHz	+34dBm	NA	T7B
UPD5731T6M	SP4T CMOS Low Power	+2.8/0	1.3@2GHz	26@2GHz	+17dBm	+20dBm	T6M
UPD5738T6N	DPDT Wide Band CMOS	+2.8/0	0.8 @ 1GHz	22 @ 1 GHz	+15dBm	+20dBm	T6N

Notes: 1. Port 3 2. Ports 1 and 2 3. Under development, please inquire

Broadband Switches to 6GHz

Part Number	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25 C)						Package
	Description	Control Voltages (V)	Insertion Loss (dB)	Isolation (dB)	Input Power @ 0.1 dB comp. point	Input Power @ 1.0 dB comp. point	
UPG2157T5F	SPDT, for WiMAX	+3.0/0	0.6 @ 3.5GHz	25 @ 3.5GHz		>37dBm	T5F
UPG2162T5N	DPDT 2.4 2.5GHz 4.9 6.0GHz	+3.0/0	0.6 @ 2.4GHz 0.85 @ 5.5GHz	30 @ 2.4 GHz 27 @ 5.5 GHz		31 dBm 29dBm	T5N
UPG2163T5N	SPDT 2.0 6.0GHz High Performance	+3.0/0	0.4 @ 2.5GHz 0.5 @ 6GHz	35 @ 2.5GHz 30 @ 6GHz		+35@2.5GHz +29@6GHz	T5N
UPG2164T5N	DPDT 2.4 2.5GHz 4.9 6.0GHz	+3.0/0	0.5 @ 2.4GHz 0.7 @ 5.5GHz	25 @ 2.4GHz 17 @ 5.5GHz		31 dBm 29dBm	T5N
UPG2176T5N	For WiMAX	+3.0/0	0.55 @ 3.5GHz	24 @ 3.5GHz		+37dBm	T5N
UPG2185T6R	SPDT 2.0 6.0GHz High Performance	+3.0/0	0.4 @ 2.5GHz 0.5 @ 6GHz	26 @ 2.5GHz 25 @ 6GHz	+29dBm	+30.5dBm	T6R
UPG2409TB	SPDT High Power for WiMAX, WLAN	+3.0/0	0.45 @ 2.5GHz 0.60 @ 3.8GHz	26 @ 2.5GHz 19 @ 3.8GHz	+33.5dBm	+35dBm	TB
UPG2409T6X	SPDT High Power for WiMAX, WLAN	+3.0/0	0.45 @ 2.5GHz 0.65 @ 6GHz	30 @ 2.5GHz 27 @ 6GHz	+34dBm	+36dBm	T6X
UPG2411T6X ¹	SPDT Dual Band WLAN 802.11a/b/g, MIMO	+3.0/0	0.4 @ 2.5GHz 0.5 @ 6GHz	25 @ 6GHz		+30.5dBm	T6X
UPG2411T7C ¹	SPDT Dual Band WLAN 802.11a/b/g, MIMO	+3.0/0	0.6 @ 2.5GHz 0.8 @ 6GHz	20 @ 6GHz		+30.5dBm	T7C
UPG2415TK	SPDT Dual Band WLAN 802.11a/b/g, MIMO	+3.0/0	0.45 @ 2.5GHz 0.65 @ 6GHz	28 @ 2.5GHz 26 @ 6GHz	+31dBm	+34dBm	TK
UPG2415T6X	SPDT Dual Band WLAN 802.11a/b/g, MIMO	+3.0/0	0.45 @ 2.5GHz 0.55 @ 6GHz	28 @ 2.5GHz 26 @ 6GHz	+31dBm	+35dBm	T6X

Notes: 1. Under development, please inquire

MobileComm Antenna Switches

Part Number	Description	Ports	Control	Typical Performance at T _A = 25 C, 50 ohms	Package Code	Package Style
UPG2193T6E	SP8T	3x WCDMA 3x GSM Rx 2x GSM Tx	SPI	0.4dB Ins Loss @ GSM LB Tx 0.6dB Ins Loss @ GSM HB Tx -80dBc 2f ₀ , 3f ₀ @ GSM LB/HB Tx +108dB IIP2 @ WCDMA-ANT	T6E	20-pin TQFN
UPG2410T6L	SP9T	3x WCDMA 4x GSM Rx 2x GSM Tx	4 Line	0.4dB Ins Loss @ GSM LB Tx 0.6dB Ins Loss @ GSM HB Tx -75dBc 2f ₀ @ GSM LB/HB Tx -75 / -72dBc 3f ₀ @ GSM LB/HB Tx	T6L	20-pin TSQFN

Low Noise GaAs FETs, 100MHz to 20GHz Typical Specifications @ TA = 25 C

Part Number	Gate Length (μm)	Gate Width (μm)	Recommended Frequency Range (GHz)	Test Frequency (GHz)	NF/Ga Bias		NF _{OPT} (dB)	GA (dB)	Power Bias		P _{1dB} (dBm)	Chip / Package Code	Chip / Package Description	Available Screening Grades
					V _{DS} (V)	I _{DS} (mA)			V _{DS} (V)	I _{DS} (mA)				
NE3210S01	0.2	160	2 to 18	12	2.0	10	0.35	13.5				S01	Plastic SMD	D
NE350184C	0.2	160	4 to 20	20	2.0	10	0.7	13.5				84C	Micro-X Ceramic	D
NE3503M04	0.2	160	2 to 18	12	2.0	10	0.55	11.5				M04	Plastic SMD	D
NE3508M04	0.6	800	0.1 to 6	2	2.0	10	0.40	14.0	3.0	30	+18.0	M04	Plastic SMD	D
NE3509M04	0.6	400	0.1 to 6	2	2.0	10	0.45	17.5	3.0	20	+14.0	M04	Plastic SMD	D
NE3509M14 ¹	0.6	400	0.1 to 6	2	2.0	10	0.4	17.5	3.0	20	+14.0	M14	Plastic SMD	D
NE3510M04	0.6	280	0.1 to 6	2	2.0	10	0.35	19.0	3.0	30	+12.0	M04	Plastic SMD	D
NE3511S02	0.2	160	4 to 18	12	2.0	10	0.30	13.5				S02	Micro-X Plastic	D
NE3512S02	0.2	160	4 to 18	12	2.0	10	0.35	13.5				S02	Micro-X Plastic	D
NE3513M04 ¹	0.2	160	10 to 14	12	2.0	6	0.45	13.0				M04	Plastic SMD	D
NE3514S02	0.2	160	4 to 20	20	2.0	10	0.75	10.0				S02	Micro-X Plastic	D
NE3515S02	0.2	200	6 to 18	12	2.0	10	0.3	12.5	3.0	25	+14.0	S02	Micro-X Plastic	D
NE3517S03			10 to 26	20	2.0	10	0.7	13.5	3.0	15	+12.0	S03	Micro-X Plastic	D
NE4210S01	0.2	160	2 to 18	12	2.0	10	0.50	13.0				S01	Plastic SMD	D

Notes: 1. Under development, please inquire

GaAs RFIC Low Noise Amplifiers

Part Number	TYPICAL ELECTRICAL CHARACTERISTICS (TA = 25 C)						Package	Application
	Frequency Range (MHz)	Test Conditions	Power Gain (dBm)	Noise Figure (dB)	I _{CC} (mA)	P _{1dB} (dBm)		
UPG2310TK	2300 to 2500	V _{CC} = 3.0 V	27	1.8	30	+13	TK	SDARS, ISM

GaAs RFIC Power Amplifiers for Handset and Wireless Applications

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25 C)				Package Style	Description	Application
	Frequency Range (MHz)	Test Conditions	Output Power (dBm)	Power Added Efficiency (%)			
UPG2118K	450 to 2500	f = 915 MHz P _{IN} = 0 dBm V _D = 3.2 V	+31.5 TYP	50 TYP	K	3 stage E-Mode Power Amplifier IC	AMR, ISM
UPG2250T5N	868 to 2500	f = 2450 MHz P _{IN} = 0 dBm V _{DD} = 1.8 V	+20 TYP	55 TYP	T5N	1.8 to 3.5 V Power Amplifier IC	Bluetooth, ZigBee, ISM
	868 to 2500	f = 2450 MHz P _{IN} = 0 dBm V _{DD} = 3.0 V	+25 TYP	58 TYP			
UPG2251T6M	2400 to 2500	f = 2450 MHz P _{IN} = -5dBm V _{DD} = 3.0 V	+25 TYP	47 TYP	T6M	3.0V Power Amplifier IC with internal matching	Bluetooth, ZigBee, ISM
UPG2301T5L	868 to 2500	f = 2450 MHz P _{IN} = +4 dBm V _{CC} = 3.3 V	+23 TYP	50 TYP	T5L	2 stage HBT Power Amplifier	Bluetooth, ZigBee, ISM
UPG2314T5N	868 to 2500	f = 2450 MHz P _{IN} = 0 dBm V _{CC} = 3 V	+20 TYP	50 TYP	T5N	Low current HBT, miniature package	Bluetooth, ZigBee, ISM

Front End ICs for Handset and Wireless Applications

Part Number	ELECTRICAL CHARACTERISTICS (T _a = 25 C)				Package Style	Description	Application
	Frequency Range (MHz)	Test Conditions	Output Power (dBm)	Power Added Efficiency (%)			
UPG2253T6S	2400 to 2500	f = 2450 MHz P _{IN} = 0 dBm V _{DD} = 3.0 V	+19 TYP	28 TYP	T6S	+19 dBm GaAs RFIC: PA, 2 SPDTs, filter, Tx/Rx bypass path	Bluetooth, ZigBee, ISM
UPG2254T6W ¹	2400 to 2500	f = 2450 MHz P _{IN} = 0 dBm V _{DD} = 3.0 V	+20 TYP	34 TYP	T6W	+20dBm GaAs RFIC: low cost version of UPG2253, miniature package	Bluetooth, ZigBee, ISM

Notes: 1. Under development, please inquire

GaAs CATV Hybrid Amplifiers

Push-Pull CATV Hybrid Amplifiers (V_{DD} = 24V, Z_S = Z_L = 75 Ω)

Part Number	Frequency (MHz, min max)	Gain (dB, min max)	CTB ¹ (dBc, max)	CSO ¹ (dBc, max)	X-MOD ^{1,2} (dBc, max)	NF ³ (dB, max)	I _{DD} (mA, max)
MC-7831	50 870	18.0 19.0	-57	-57	-50	7.0	240
MC-7831-HA	40 1000	18.0 19.0	-57	-57	-50	7.0	240
MC-7832	50 870	22.0 23.0	-57	-57	-50	6.5	240
MC-7832-HA	40 1000	22.0 23.0	-57	-57	-50	6.5	240
MC-7833	50 870	25.0 26.0	-57	-57	-50	6.0	240
MC-7834-KC ⁴	50 870	20.0 21.0	-59	-59	-52	7.0	325
MC-7836	50 870	27.0 28.0	-58	-58	-52	6.0	260

Notes: 1. Distortion measurements at V_{OUT} = 44 dBm V flat, 110 channels. 2. Measured using EIAJ methods and procedures.
3. Noise Figure measured at 870 MHz. 4. Higher current device for better X-mod and crash point performance.

Power Doubler CATV Hybrid Amplifiers (V_{DD} = 24V, Z_S = Z_L = 75 Ω)

Part Number	Frequency (MHz, min max)	Gain (dB, min max)	CTB (dBc, typ)	CTB (dBc, max)	CSO (dBc, typ)	CSO (dBc, max)	X-MOD ¹ (dBc, typ)	X-MOD ¹ (dBc, max)	I _{DD} (mA, max)
MC-7845 ²	50 870	18.0 19.0	-63	-60	-68	-63	-59	-55	375
MC-7846 ²	50 870	22.0 23.0	-63	-60	-67	-63	-60	-55	375
MC-7847 ²	50 870	25.0 26.0	-65	-60	-67	-63	-62	-55	375
MC-7847-KC ³	50 870	25.0 26.0		-60		-63		-55	420
MC-7881 ⁴	50 870	18.0 19.0		-60		-63		-55	360
MC-7882 ⁴	50 870	20.0 21.0		-60		-63		-55	360
MC-7883 ⁴	50 870	22.0 23.0		-60		-63		-55	360
MC-7884 ⁴	50 870	25.0 26.0		-60		-63		-55	360
MC-7891 ⁵	40 1000	18.0 19.5		-63		-65		-60	385
MC-7893 ⁵	40 1000	22.5 24.0		-63		-65		-60	385
MC-7894 ⁵	40 1000	24.5 25.5		-63		-65		-60	385
MC-7896 ⁵	40 1000	27.0 28.0		-63		-65		-60	385

Notes: 1. Measured using EIAJ methods and procedures.
2. Distortion measurements are made with 110 channels loading, V_{OUT} = +50dBmV at 745.25 MHz, 10dB tilted across the band.
3. Higher current device for better X-mod and crash point performance.
4. Distortion measurements are made with 110 channels loading, V_{OUT} = +52dBmV at 745.25 MHz, 10dB tilted across the band.
5. Distortion measurements are made with 77 channels loading, V_{OUT} = +52dBmV at 547.25 MHz, 7 dB tilted across the band.

Silicon LD-MOSFETs Typical Specifications @ TC = 25 C

Part Number	P _{OUT} (dBm) TYP	Linear Gain (dB) TYP	Test Conditions				Package Description
			Freq (GHz)	P _{IN} (dBm)	V _{DS} (V)	I _{DSQ} (mA)	
NE552R479A	26.0	11	2.45	19	3.0	200	79A Pkg: Compact SMT
NE5511279A	40.0	15.0	0.9	27	7.5	400	79A Pkg: Compact SMT
NE5520279A	32.0	10	1.8	25	3.2	700	79A Pkg: Compact SMT
NE5520379A	35.5	16	0.9	25	3.2	600	79A Pkg: Compact SMT
	33.0	8.5	1.8				
NE5531079A	40.0	20.5	0.46	25	7.5	200	79A Pkg: Compact SMT
NE55410GR	40.4	25	2.1	16	28	120	GR Pkg: 16 pin plastic HTSSOP
NE5500234	32.5	11	1.9	25	4.8	400	34 Pkg: Compact SMT

Small Signal Silicon Bipolar Transistors

Silicon Transistors

Part Number	TEST f (GHz)	NF/GA		NF TYP (dB)	GA TYP (dB)	MAG/MSG			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Package Name, Description
		V _{CE} (V)	I _{CQ} (mA)			V _{CE} (V)	I _C (mA)	TYP (dB)				
NE661M04	2.0	2	2	1.2	16	2	10	22	22	100	10	M04 Pkg: 4 pin low profile SOT-343 style
NE662M04	2.0	2	5	1.1	16	2	20	20	23	70	35	M04 Pkg: 4 pin low profile SOT-343 style
NE662M16	2.0	2	5 / 20	1.1	17	2	20	19	25	70	35	M16 Pkg: 6 pin low profile, recessed leads
NE66219	2.0	2	5	1.5	12.0	2	20	14	21	80	35	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE68018	2.0	6	5	1.8	10.0	1	1	12.5	10	100	35	18 Pkg: 4 pin Super Mini Mold
NE68019	2.0	3	5	1.9	9.0	1	1	12.0	8	120	35	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE68030	2.0	6	5	1.7	9.5	6	10	8.5	10	100	35	30 Pkg: 3 pin Super Mini Mold, SOT-323 style
NE68033	2.0	6	5	1.8	9.0	6	10	8.0	10	100	35	33 Pkg: 3 pin Mini Mold, SOT-23 style
NE68039	2.0	6	5	1.7	11.0	6	10	9.0	10	100	35	39 Pkg: 4 pin Mini Mold
NE68118	1.0	2.5	3	1.1	13.0	2.5	3	16.0	9	100	65	18 Pkg: 4 pin Super Mini Mold
NE68119	1.0	2.5	3	1.1	12.0	2.5	3	15.5	7	120	65	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE68130	1.0	8	7	1.5	13.5	8	20	13.0	7	120	65	30 Pkg: 3 pin Super Mini Mold, SOT-323 style
NE68133	1.0	8	7	1.2	13.0	8	20	11.0	9	100	65	33 Pkg: 3 pin Mini Mold, SOT-23 style
NE68139	1.0	8	7	1.2	13.5	8	20	15.0	9	100	65	39 Pkg: 4 pin Mini Mold, SOT-143 style
NE68518	2.0	2.5	3	1.5	8.5	2.5	3	12.0	12	110	30	18 Pkg: 4 pin Super Mini Mold
NE68519	2.0	2.5	3	1.5	7.5	2.5	3	11.0	12	110	30	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE68539	2.0	2.5	3	1.5	7.5	2.5	3	11.5	12	110	35	39 Pkg: 4 pin Mini Mold, SOT-143 style
NE68618	2.0	1	3	1.5	9	1	3	13	15	100	10	18 Pkg: 4 pin Super Mini Mold
NE68619	2.0	1	3	1.5	8.5	1	3	12.5	12	100	10	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE68718	2.0	1	3	1.3	8	1	3	11	13	100	30	18 Pkg: 4 pin Super Mini Mold
NE68719	2.0	1	3	1.3	7.5	1	3	10	9	100	30	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE851M13	2.0	1	10	1.9	5.5	1	5	4.0	6.5	120	100	M13 Pkg: 3 pin low profile, ultra-miniature
NE85618	1.0	2.5	3	1.4	11.0	2.5	3	14.0	6.5	120	100	18 Pkg: 4 pin Super Mini Mold
NE85619	1.0	2.5	3	1.5	10.0	2.5	3	13.5	4.5	120	100	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NE85630	1.0	10	7	1.3	12.0	10	20	12.0	4.5	110	100	30 Pkg: 3 pin Super Mini Mold, SOT-323 style
NE85633	1.0	10	7	1.4	9.0	10	20	11.5	7	120	100	33 Pkg: 3 pin Mini Mold, SOT-23 style
NE85639	1.0	10	7	1.5	13.5	10	20	13.0	7	120	100	39 Pkg: 4 pin Mini Mold, SOT-143 style
NE894M13	2.0	1	5	1.4	13	1	20	13.0	20	80	35	M13 Pkg: 3 pin low profile, ultra-miniature
NE97733	1.0	8	3	1.5	10.0	8	20	12.0	8.5	60	50	33 Pkg: 3 pin Mini Mold, SOT-23 style (PNP)
NE97833	1.0	10	3	2.0	7.0	10	15	10.0	5.5	40	50	33 Pkg: 3 pin Mini Mold, SOT-23 style (PNP)

SiGe Transistors

Part Number	TEST f (GHz)	NF/GA		NF TYP (dB)	GA TYP (dB)	MAG/MSG			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Package Name, Description
		V _{CE} (V)	I _{CO} (mA)			V _{CE} (V)	I _C (mA)	TYP (dB)				
NESG2021M05	2	2	3	0.9	18.0	3	10	22.5	25	195	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG2021M05	5.2	2	3	1.3	10.0	—	—	—	—	195	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG2021M16	2	2	3	0.9	18	3	10	22.5	25	190	35	M16 Pkg: 6 pin low profile, recessed leads
NESG2030M04	2	2	5	0.9	16	2	20	20	60	300	35	M04 Pkg: 4 pin low profile SOT-343 style
NESG2031M05	2	2	5	0.8	17.0	3	20	21.5	—	195	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG2031M05	5.2	2	5	1.3	10.0	—	—	—	—	195	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG2031M16	5.2	2	5	1.3	10	3	20	21.5	25	190	35	M16 Pkg: 6 pin low profile, recessed leads
NESG204619	2	1	3	0.8	11.0	—	—	—	18	180	40	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NESG2101M16	2	2	10	0.9	13.0	3	50	17.0	17	190	100	M16 Pkg: 6 pin low profile, recessed leads
NESG210719	2	1	5	0.9	9.0	—	—	—	10	180	100	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style
NESG3031M05	5.2	2	6	0.95	10.0	—	—	—	—	300	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG3031M05	5.8	2	6	1.1	9.5	3	20	14.0	—	300	35	M05 Pkg: 4 pin low profile SOT-343 style
NESG3031M14	5.2	2	6	0.95	10.0	—	—	—	—	300	35	M14 Pkg: 4 pin low profile, recessed leads
NESG3031M14	5.8	2	6	1.1	9.5	3	20	15.0	—	300	35	M14 Pkg: 4 pin low profile, recessed leads
NESG3032M14	2.0	2	6	0.6	17.5	3	20	20.5	—	300	35	M14 Pkg: 4 pin low profile, recessed leads
NESG3033M14	2.0	2	6	0.6	17.5	3	20	20.5	—	300	35	M14 Pkg: 4 pin low profile, recessed leads
NESG4030M14	5.8	2	6	1.1	11.5	—	—	—	—	400	35	M14 Pkg: 4 pin low profile, recessed leads

Medium Power Silicon Transistors

Part Number	TEST f (GHz)	P _{1dB}			MAG / MSG			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Package Description
		V _{CE} (V)	I _{CO} (mA)	TYP (dBm)	V _{CE} (V)	I _C (mA)	TYP (dB)				
NE46134	1.0	12.5	100	27.5	10	50	9	5.5	100	250	34 Pkg: 4 pin SOT-89 style
NE461M02	1.0	12.5	100	27.5	10	50	11	5.5	120	250	M02 Pkg: 4 pin high gain SOT-89 style
NE663M04	2.0	2	50	16	2	50	15	18	100	100	M04 Pkg: 4 pin low profile SOT-343 style
NE664M04	1.8	3.6	200	26	3	100	12	20	60	500	M04 Pkg: 4 pin low profile SOT-343 style
NE677M04	1.8	2.8	23	15	3	20	16	15	120	50	M04 Pkg: 4 pin low profile SOT-343 style
NE678M04	1.8	2.8	40	18	3	30	13.5	12	120	100	M04 Pkg: 4 pin low profile SOT-343 style
NE85634	1.0	10	40	22	10	40	11	6.5	120	100	34 Pkg: 4 pin SOT-89 style
NE856M02	1.0	10	40	22	10	50	14	6.5	120	100	M02 Pkg: 4 pin high gain SOT-89 style
NESG2101M05 ¹	2.0	3.6	10	21	3	50	17	17.0	195	100	M05 Pkg: 4 pin low profile SOT-343 style
NESG250134 ¹	0.5	3.6	30	29	3.6	100	23	10	120	500	34 Pkg: 4 pin SOT-89 style
NESG250134 ¹	0.9	3.6	30	29	—	—	—	10	120	500	34 Pkg: 4 pin SOT-89 style
NESG260234 ¹	0.46	6.0	30	30	6	100	23	15	120	600	34 Pkg: 4 pin SOT-89 style
NESG260234 ¹	0.9	6.0	30	30	—	—	—	10	120	600	34 Pkg: 4 pin SOT-89 style
NESG270034 ¹	0.46	6.0	30	33.5	—	—	—	15	120	750	34 Pkg: 4 pin SOT-89 style
NESG270034 ¹	0.9	6.0	30	31.5	—	—	—	15	120	750	34 Pkg: 4 pin SOT-89 style
UPA901TU	5.8	3.6	90	19	3.6	52	25	—	120	300	TU Pkg: 8 pin Mini Mold

Note: 1. SiGe part

Silicon Transistors For Cordless Phones

Part Number	Frequency Range	P _{1dB} (dBm)	Linear Gain (dB)	Collector Efficiency (%)	V _{CE} (V)	Frequency (MHz)	Package Description
NE68939	500-2000	24.5	8	62	3.6	1900	39 Pkg: 4 pin Mini Mold, SOT-143 style
NE69039	500-2000	27.5	6	72	3.6	1900	39 Pkg: 4 pin Mini Mold, SOT-143 style

Twin Transistors

Part Number	TEST f (GHz)	NF/GA V _{CE} (V)	NF/GA I _C (mA)	NF TYP (dB)	GA TYP (dB)	MAG (dB)	S _{21E} ²			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Pkg. Code	Package Style	Die
							V _{CE} (V)	I _C (mA)	TYP (dB)						

Twin Transistors in a single package – Matched Die

UPA800T	2.0	3	5	1.9	9.0	12.0	3	5	7.5	8	120	35	S06	SOT-363	NE680
UPA801T	1.0	3	7	1.2	10.0	14.0	3	7	9.0	4.5	120	100	S06	SOT-363	NE856
UPA802T	1.0	3	7	1.4	14.0	16.0	3	7	12.0	7.0	100	65	S06	SOT-363	NE681
UPA806T	2.0	3	3	1.5	7.5	11.0	3	10	8.5	12.0	110	30	S06	SOT-363	NE685
UPA807T	2.0	2	3	1.5	10.0	13.5	2	7	9.0	13.0	100	10	S06	SOT-363	NE686
UPA808T	2.0	2	3	1.3	8.0	11.0	2	20	8.5	11.0	100	30	S06	SOT-363	NE687
UPA810T	1.0	3	7	1.2	10.0	14.0	3	7	9.0	4.5	120	100	S06	SOT-363	NE856
UPA811T	2.0	3	5	1.9	9.0	12.0	3	5	7.5	8	120	35	S06	SOT-363	NE680
UPA812T	1.0	3	7	1.4	14.0	16.0	3	7	12.0	7.0	100	65	S06	SOT-363	NE681
UPA828TD	2.0	2	3	1.3	10.0	11	2	20	8.5	11.0	100	30	TD	Miniature Recessed Leads	NE687
UPA895TD	2.0	1	10	1.9	9.0	10.0	1	15	5.5	5	120	100	TD	Miniature Recessed Leads	NE851

Twin Transistors in a single package – Mixed Die

UPA861TD	(Q1)	2.0	1	3	1.5	9	11	1	10	9	12	105	30	TD	Miniature Recessed Leads	NE687
	(Q2)	2.0	1	5	1.4	12.5	13.5	1	20	13	20	75	35			NE894
UPA862TD	(Q1)	2.0	3	3	1.5	9.5	12.5	3	10	8.5	12	110	30	TD	Miniature Recessed Leads	NE685
	(Q2)	2.0	1	10	1.9	9	10	1	15	5.5	6.5	120	100			NE851
UPA863TD	(Q1)	2.0	1	3	1.5	9	11	1	10	9	12	105	30	TD	Miniature Recessed Leads	NE687
	(Q2)	2.0	1	10	1.9	9	10	1	15	5.5	6.5	120	100			NE851

Silicon Transistor Chips

Part Number	TEST f (GHz)	NF/GA V _{CE} (V)	NF/GA I _C (mA)	NF TYP (dB)	GA TYP (dB)	MAG TYP (dB)	S _{21E} ²			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Pkg. Code	Die
							V _{CE} (V)	I _C (mA)	TYP (dB)					
NE46100	1.0	10	50	2.0	7.0	9.8	10	100	10	5.5	100	250	00	NE461
NE66100	2.0	2	2	1.2	16.5	22.0	2	5	17	25	70	12	00	NE661
NE66200	2.0	2	5	1.1	16.0	19.0	2	20	17	25	70	35	00	NE662
NE66300	2.0	2	10	1.2	17.5	14.0	2	50	11	25	70	100	00	NE663
NE68000	4.0	6	5	2.6	8.0	12.5	6	10	9.0	10.0	100	35	00	NE680
NE68100	2.0	8	7	1.6	12.0	19	8	20	14.0	9.0	100	65	00	NE681
NE85600	2.0	10	7	2.1	10.0	16	10	20	9.0	7.0	120	100	00	NE856
NESG303100G	2.4/5.8	2	6	0.6/1.1	16.0/9.5	14	3	20	8.5	110	300	35	00	NESG3031

Silicon Oscillator Transistors

Part Number	P _{osc}				f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Pkg. Code	Package Description
	f (GHz)	V _{CE} (V)	I _C (mA)	TYP (W)					
NE58219	0.9	5.0	5.0	0.001	5.0	90	60	19	19 Pkg: 3 pin Ultra-Super Mini Mold, SC-90 style

Silicon Switching Transistors

Part Number	C _{CB} V _{CB} (V)	C _{CB} TYP (pF)	f _T TYP (GHz)	Typical Switching Times						S _{21E} ²				h _{FE} TYP	I _C MAX (mA)	Pkg. Code	Package Description
				V _{CE} (V)	I _C (mA)	T _{d(ON)} (ns)	T _r (ns)	T _{d(OFF)} (ns)	T _f (ns)	f (GHz)	V _{CE} (V)	I _C (mA)	TYP (dB)				
NE68100	10	0.2	9.0	8	15	0.3		0.2		2.0	8	20	11.0	100	65	00	Chip
NE68118	10	.25	9.0	8	15	0.4		0.3		1.0	8	20	15.0	100	65	18	18 Pkg: 4 pin Super Mini Mold
NE68119	3	.45	7.0	8	15	0.6		0.5		1.0	3	7	12.0	100	65	19	19 Pkg: 3 pin SC-90 style
NE68133	10	.35	9.0	8	15	0.4		0.3		1.0	8	20	13.0	100	65	33	33 Pkg: 3 pin SOT-23 style

Low Power Amplifiers

Part Number	Typical Frequency Range @ 3dB down (MHz)	ELECTRICAL CHARACTERISTICS ¹ (T _A = 25 C)											Package Code	Package Style	
		V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)			RLIN (dB)	RLOUT (dB)	P _{1dB} (dBm)			ISOL (dB)
			MIN	TYP	MAX	TYP	MIN	TYP	MAX	TYP	TYP	TYP			TYP
UPC2745TB ²	2700	3	5	7.5	10	6.0	9	12	14	11	5.5	-3.0	38	S06 / TB	SOT-363
UPC2746TB ²	1500	3	5	7.5	10	4.0	16	19	21	13	8.5	-3.7	45	S06 / TB	SOT-363
UPC2747TB ³	1800	3	3.8	5	7	3.3	9	12	14	14	10	-10.9	40	S06 / TB	SOT-363
UPC2748TB ³	1500	3	4.5	6	8	2.8	16	19	21	11.5	8.5	-8.5	40	S06 / TB	SOT-363
UPC2749TB ⁴	2900	3	4	6	8	4	13	16	18.5	10	13	-12.5	30	S06 / TB	SOT-363
UPC3237TK ²	1000	3	3.5	5.0	7	1.4	13.0	15.3	17.5	10	14	-5.5	22	TK	6 pin Recessed Lead
UPC8151TB ⁵	Note 6	3	2.8	4.2	5.8	6.0	9.5	12.5	14.5	5	10	+2.5	38	S06 / TB	SOT-363
UPC8178TB ⁴	Note 7	3	1.4	1.9	2.4	5.5	9.0	11.5	13.5	8		-7	40	S06 / TB	SOT-363
UPC8179TB ⁴	Note 7	3	2.9	4.0	5.4	5.0	13.0	15.5	17.5	7		1.5	42	S06 / TB	SOT-363
UPC8179TK ⁴	Note 7	3	2.9	4.0	5.4	5.0	13.0	15.5	17.5	7	-	0.5	42	TK	6 pin Recessed Lead

Notes: 1. Z_L = 50 Ω for all Electrical Characteristics 2. f = 500 MHz test condition 3. f = 900 MHz test condition 4. f = 1900 MHz test condition
5. f = 1000 MHz test condition 6. 100–1900MHz with output port matching 7. 100–2400MHz with output port matching

Wideband Amplifiers

Part Number	Typical Frequency Range @ 3dB down (MHz)	ELECTRICAL CHARACTERISTICS ¹ (T _A = 25 C)											Package Code	Package Style	
		V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)			RLIN (dB)	RLOUT (dB)	P _{1dB} (dBm)			ISOL (dB)
			MIN	TYP	MAX	TYP	MIN	TYP	MAX	TYP	TYP	TYP			TYP
UPC2708TB ³	2900	5	20	26	33	6.5	13	15	18.5	11	20	+9.2	23	S06 / TB	SOT-363
UPC2709TB ³	2300	5	19	25	32	5.0	21	23	26.5	10	10	+8.7	31	S06 / TB	SOT-363
UPC2710TB ²	1000	5	16	22	29	3.5	30	33	36.5	6	12	+10.8	39	S06 / TB	SOT-363
UPC2711TB ³	2900	5	9	12	15	5.0	11	13	16.5	25	12	-2.6	30	S06 / TB	SOT-363
UPC2712TB ³	2600	5	9	12	15	4.5	18	20	23.5	12	13	-0.4	33	S06 / TB	SOT-363
UPC2762TB ⁴	2900	3		27	35	7.0	11.5	15.5	17.5	8.5	12	+7	25	S06 / TB	SOT-363
UPC2763TB ⁴	2700	3		27	35	5.5	18	21	24	11	9	+6.5	29	S06 / TB	SOT-363
UPC2771TB ⁵	2100	3		36	45	6	19	21	24	14	10	+11.5	30	S06 / TB	SOT-363
UPC2776TB ³	2700	5	18	25	33	6.0	21	23	26	7.5	20	+6	32	S06 / TB	SOT-363
UPC3215TB ⁴	2900	5		14		2.3	18.5	20.5		15	9.5	+1.5	44	S06 / TB	SOT-363
UPC3223TB ³	3200	5	15	19	24	4.5	20.5	23	22.5	12	12	+6.5	33	S06 / TB	SOT-363
UPC3224TB ³	3200	5	7.0	9.0	12.0	4.3	19	21.5	24	12	17	-3.5	40	S06 / TB	SOT-363
UPC3225TB ³	2800	5	20.0	24.5	31.0	3.7	30	32.5	35	8.5	10.5	+9.0	41	S06 / TB	SOT-363
UPC3226TB ³	3200	5	12.5	15.5	19.5	5.3	22	24	26	14	13	+7.5	34	S06 / TB	SOT-363
UPC3227TB ³	3200	5	4.0	4.8	6.0	4.7	20.5	22.5	24.5	10.5	13.5	-6.5	40	S06 / TB	SOT-363
UPC3232TB ³	3200	5	20	26	32	4.0	30	32.8	35.5	9.5/13	10/14.5	+11	41	S06 / TB	SOT-363
UPC3236TK ³	3000	5	19	24	31	2.6	36	38	41	9	11	+10	50	TK	6-pin Recessed Lead
UPC3239TB ³	3000	3.3	23	29	37	4.2	22	25	28	15	25	+9	35	S06 / TB	SOT-363
UPC3240TB ³	3000	3.3	9.5	13	17	4.3	22	25	28	23	12	+1	42	S06 / TB	SOT-363
UPC3241TB ³	3000	3.3	15	19.8	25	4.0	20.5	23.5	26.5	20	17	+7.5	32	S06 / TB	SOT-363
UPC3242TB ^{3,6}	3000	3.3		4.3		3.5		22		10	10	+10.5		S06 / TB	SOT-363
UPC8181TB ⁴	4000	3		23	30	4.5	18	21	24	10.5	10	+7	32	S06 / TB	SOT-363
UPC8182TB ⁴	2900	3	22	30	38	4.5	17.5	20.5	23.5	0	11	+9.0	32	S06 / TB	SOT-363

Notes: 1. Z_L = 50 Ω for all Electrical Characteristics 2. f = 500 MHz test condition 3. f = 1000 MHz test condition 4. f = 1900 MHz test condition
5. f = 900 MHz test condition 6. Under development, please inquire

SiGe and SiGe:C Low Noise Amplifiers

Part Number	Typical Frequency (GHz)	ELECTRICAL CHARACTERISTICS ¹ (T _A = 25°C)											Package Code	Package Style	
		V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)			RL _{IN} (dB)	RL _{OUT} (dB)	Input P _{1dB} (dBm)			ISOL (dB)
			MIN	TYP	MAX	TYP	MIN	TYP	MAX	TYP	TYP	TYP			TYP
UPC8211TK ¹	3.0 ²	3	—	3.5	4.5	1.3	15.5	18.5	21.5	-7.5	14.5	-24	32	TK	6 pin Recessed Lead
UPC8215TU ¹	1.575	3		10.0	13.0	1.3	24.0	27.0	30.0	-7.0	-14.0	-22	40	TU	8 pin Recessed Lead
UPC8230TU ³	1.575 ²	3		6.0		0.85		18.5		-16	-15	-17		TU	8 pin Recessed Lead
UPC8231TK ³	1.575 ²	3	—	3.5	—	0.80	—	20.0	—	-13	-14	-22	—	TK	6 pin Recessed Lead
UPC8232T5N ³	1.575	3		3.0		0.95		17.0		-14	-16	-22		T5N	6 pin Leadless
UPC8233TK ³	1.575 ²	1.8	—	3.5	—	0.95	—	20.0	—	-16	-16	-23	36	TK	6 pin Recessed Lead
UPC8236T6N ³	1.575	1.8		6.5		0.8		19.5		-11	-14	-18	39	T6N	6 pin Leadless
UPC8240T6N ³	1.575	3	4.5	6.5	9.0	1.0	24.5	28	31	8.5	17	-22.5	55	T6N	6 pin Leadless
UPC8244T6N ^{3,4}	1.575	3	3	6.5	10.0	0.9	14.0	18.5	20					T6N	6 pin Leadless

Notes: 1. SiGe device 2. 0.8 to 3.0GHz 3. SiGe:C device 4. Under development, please inquire

SiGe BiCMOS Wideband LNA with Bypass

Part Number	Mode	ELECTRICAL CHARACTERISTICS (T _A = 25°C)											Package Code	Package Style
		Typical Frequency Range @ 3 dB Down (MHz)	V _{CC} (V)	I _{CC} (mA)	NF (dB)	Gain (dB)			RL _{IN} (dB)	RL _{OUT} (dB)	Input P _{1dB} (dB)	Input IP ₃ (dB)		
						TYP	TYP	MIN	TYP	MAX	TYP	TYP		
UPD5740T6N	LNA	770	2.8	5.0	1.5	11.5	13.5	15.5	10	11	-5.0	+2	T6N	8 pin SSOP
	Bypass	770		1μA		-2.0	-1.3		17.0	17.0	+8	+30		
UPD5750 ¹	LNA	770	1.8	3	1.4		13.0			8	-11	-8	Ball Grid	WL-BGA
	Bypass	770		1μA			-1.5			8	+30			

Notes: 1. Under development, please inquire

AGC Amplifiers with Video Output

Part Number	ELECTRICAL CHARACTERISTICS (T _A = 25°C)											Package Code	Package Style	
	Typical Frequency Range @ 3 dB Down (MHz)	V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)		RL _{IN} (dB)	RL _{OUT} (dB)	V _{OUT} ² (p-p)			AGC (dB)
			MIN	TYP	MAX		TYP	MIN	MAX	TYP	TYP			TYP
UPC3217GV ¹	100	5	15	23	34	6.5	0	53	N/A	N/A	1.0	53	S08 / GV	8 pin SSOP
UPC3218GV ¹	100	5	15	23	34	3.5	10	63	N/A	N/A	1.0	53	S08 / GV	8 pin SSOP
UPC3219GV ¹	100	5	28	35	42	9	0	42	N/A	N/A	1.0	42	S08 / GV	8 pin SSOP
UPC3221GV ¹	100	5	26	33	41	4.2	10	60	N/A	N/A	1.0	50	S08 / GV	8 pin SSOP
UPC3231GV ¹	90	5	28	36	44	5.0	4	65	N/A	N/A	1.0	61	S08 / GV	8 pin SSOP
UPC3234GV ¹	100	5	—	28.5	38	4.0	4.5	63	N/A	N/A	1.0	58.5	S08 / GV	8 pin SSOP

Notes: 1. f_{IN} = 45 MHz, Z_S = 50Ω, Z_L = 250Ω 2. Output Voltage swing into RL = 250Ω, V_{OUT} = 1.0 V_{p-p} 3. Digital output path indicated. Gain (max) for separate analog path = 28dB

Variable Gain Amplifiers

Part Number	ELECTRICAL CHARACTERISTICS (T _A = 25°C)											Package Code	Package Style	
	Typical Frequency Range @ 3 dB Down (MHz)	V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)		RL _{IN} (dB)	RL _{OUT} (dB)	V _{OUT} ² (V)			AGC (dB)
			MIN	TYP	MAX		TYP	TYP	MAX	TYP	TYP			TYP
UPC8204TK ¹	800 – 2500	3	8.5	11.5	15	7.5	-26	+14	13	—	+5	40	TK	6 pin recessed lead

Notes: 1. f = 2.5 MHz, 50Ω in and out, -20dBm input power 2. At Maximum Gain

DC to VHF Differential Amplifier

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25°C)											Package Code	Package Style	
	Video Amp						AGC Amp							
	V (V)	Vcc (mA)	Avd ^{1,2}		BW ^{2,3} (MHz)		V _{op-p} (V _{p-p})	Vcc (V)	Icc (mA)	Gain (dB)	AGC (dB)			NF (dB)
			Icc	Gain 1	Gain 2	Gain 1								
TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP				
UPC81663GV ⁴	±6	13	320	10	120	700	4.0	—	—	—	—	S08 / GV	8 pin SSOP	

Notes: 1. Differential Voltage Gain 2. Operation conditions applicable to AVd and BW:
 Gain 1 – Gain select pins G1A and G1B are shorted
 Gain 2 Gain select pins G1A and G1B are open 3. BW refers to Gain 3dB down from 100kHz
 4. f = 10 MHz test condition

Frequency Upconverters

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25 C)								Package Code	Package Style
	IF Input Frequency Range @3 dB Down (MHz)	RF Output Frequency Range (MHz)	Vcc (V)	Icc (mA)	Conversion Gain (dB)	Psat ¹ (dBm)	Noise Figure (dB)	OIP ₃		
	TYP	TYP								
UPC8106TB ²	50-400	400-2000	3.0	9.0	10.0	-2.0	8.5	+5.5	S06 / TB	SOT-363
UPC8172TB ³	50-400	800-2500	3.0	9.0	8.5	0.0	10.4	+6.0	S06 / TB	SOT-363
UPC8187TB ⁴	50-400	800-2500	3.0	15	11	+2.5	12	+10.0	S06 / TB	SOT-363

Notes: 1. Pin = 0 dBm 2. RF = 900 MHz, LO = 660 MHz, PLO = -5 dBm 3. RF = 1900 MHz, LO = 1660 MHz, PLOIN = -5 dBm
 4. RF = 1900 MHz, LO = 1780 MHz, PLO = -5 dBm

Frequency Downconverters

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25 C)								Package Code	Package Style
	RF Input Frequency Range @3 dB Down (MHz)	IF Output Frequency Range @3 dB Down (MHz)	Vcc (V)	Icc (mA)	Conversion Gain (dB)	Psat (dBm)	Noise Figure (dB)	Test Condition (Note)		
	TYP	TYP								
UPC2756TB	100-2000	10-300	3.0	5.9	14	-12	13	3	S06 / TB	SOT-363
UPC2757TB	100-2000	20-300	3.0	5.6	13	-8	13	4	S06 / TB	SOT-363
UPC2758TB	100-2000	20-300	3.0	11	17	-4	13	4	S06 / TB	SOT-363
UPC8112TB	800-2000	100-300	3.0	8.5	13	-3	11.2	5	S06 / TB	SOT-363

Note: 1. AGC Amp and Mixer Block only

Out-of-Band Tuners: Downconverter with AGC & Video Amplifiers for CATV/Settop Box

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25 C)							Package Code	Package Style
	RF Input Frequency Range (MHz)	Vcc (V)	Icc (mA)	Conversion Gain (dB)	Gain Control Range (dB)	Noise Figure (dB)	IM3 (dBc) Code		
UPC3220GR	30 250	5.0	84	33	46	7.0	55	S16	16 pin SSOP
UPC3228T5S	20 800	5.0	85	28	70	8.3	57	T5S	32 pin QFN
UPC3243T7A	50 300	5.0	82	28	60	7.5	55	T7A	28 pin QFN

Prescalers (Frequency Dividers)

Part Number	ELECTRICAL CHARACTERISTICS (TA = 25 C)						Divide Ratio	Package Code	Package Style		
	f _{in} (GHz)		P _{in} (dBm)		P _{out} ¹ (dBm)	Vcc (V)				Icc (mA)	
	MIN	MAX	MIN	MAX						MIN	MAX
UPB1507GV	0.5	3.0	-15	+6	Note 1	5.0	12.5	26.5	64/128/256	S08 / GV	8 pin SSOP
UPB1508GV	0.5	3.0	-10	+10	-7	5.0	12 (TYP)		2	S08 / GV	8 pin SSOP
UPB1509GV	0.05	1.0	-20	-5	Note 2	2.2 to 5.5	5.3 (TYP)		2/4/8	S08 / GV	8 pin SSOP
UPB1510GV	0.5	3.0	-15	+6	-7	5.0	15 (TYP)		4	S08 / GV	8 pin SSOP
UPB1513TU	5	13	-8	0	-4.0	5.0	48 (TYP)		4	S08 / TU	8 pin L ² mm

Notes: 1. Output voltage swing with CL = 8 pF, VOUT = 1.2 Vp-p minimum 2. Output voltage swing with RL = 200 Ω, VOUT = 0.1 Vp-p minimum

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